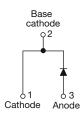
VS-HFA08TB120-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



www.vishay.com



| PRIMARY CHARACTERISTICS | | | | | |
|----------------------------------|-------------|--|--|--|--|
| I _{F(AV)} | 8 A | | | | |
| V _R | 1200 V | | | | |
| V _F at I _F | 2.4 V | | | | |
| t _{rr} typ. | 28 ns | | | | |
| T _J max. | 150 °C | | | | |
| Package | TO-220AC 2L | | | | |
| Circuit configuration | Single | | | | |

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- \bullet Designed and qualified according to JEDEC $^{\circledast}\text{-}\text{JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB120 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|--|-----------------------------------|-------------------------|-------------|-------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | |
| Cathode to anode voltage | V _R | | 1200 | V | | |
| Maximum continuous forward current | I _F | T _C = 100 °C | 8 | | | |
| Single pulse forward current | I _{FSM} | | 130 | А | | |
| Maximum repetitive forward current | I _{FRM} | | 32 | | | |
| Maximum neuror dissinction | P _D | T _C = 25 °C | 73.5 | W | | |
| Maximum power dissipation | | T _C = 100 °C | 29 | vv | | |
| Operating junction and storage temperature range | T _J , T _{Stg} | | -55 to +150 | °C | | |

Revision: 16-Dec-2021



For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





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| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | | |
|--|-----------------|--|------|------|------|-------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | |
| Cathode to anode breakdown voltage | V _{BR} | I _R = 100 μA | 1200 | - | - | | | |
| | V _{FM} | I _F = 8.0 A | - | 2.6 | 3.3 | V | | |
| Maximum forward voltage | | I _F = 16 A | - | 3.4 | 4.3 | | | |
| | | I _F = 8.0 A, T _J = 125 °C | - | 2.4 | 3.1 | | | |
| Maximum reverse | | $V_{R} = V_{R}$ rated | - | 0.31 | 10 | | | |
| leakage current | IRM | $T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ | - | 135 | 1000 | μA | | |
| Junction capacitance | CT | V _R = 200 V | - | 11 | 20 | pF | | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 8.0 | - | nH | | |

| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \degree C$ unless otherwise specified) | | | | | | | | |
|--|---------------------------|---|--|------|------|------|-------|--|
| PARAMETER | SYMBOL | TEST CO | NDITIONS | MIN. | TYP. | MAX. | UNITS | |
| | t _{rr} | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$ | A/μs, V _R = 30 V | - | 28 | - | | |
| Reverse recovery time | t _{rr1} | T _J = 25 °C | | - | 63 | 95 | ns | |
| | t _{rr2} | T _J = 125 °C | I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V | - | 106 | 160 | | |
| Deal and a second | I _{RRM1} | T _J = 25 °C | | - | 4.5 | 8.0 | | |
| Peak recovery current | I _{RRM2} | T _J = 125 °C | | - | 6.2 | 11 | A | |
| Poweree recevery charge | Q _{rr1} | T _J = 25 °C | | - | 140 | 380 | nC | |
| Reverse recovery charge | Q _{rr2} | T _J = 125 °C | | - | 335 | 880 | nc | |
| Peak rate of recovery current | dl _{(rec)M} /dt1 | T _J = 25 °C | | - | 133 | - | A/µs | |
| during t _b | dl _{(rec)M} /dt2 | T _J = 125 °C | | - | 85 | - | γγµs | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | |
|---|-------------------|---|--------------|-------|------------|------------------------|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS | | |
| Lead temperature | T _{lead} | 0.063" from case (1.6 mm) for 10 s | - | - | 300 | °C | | |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 1.7 | | | |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | - | 40 | K/W | | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth, and greased | - | 0.25 | - | | | |
| Weight | | | - | 6.0 | - | g | | |
| weight | | | - | 0.21 | - | oz. | | |
| Mounting torque | | | 6.0 (5.0) | - | 12 (10) | kgf · cm (lbf · in) | | |
| Marking device | | Case style 2L TO-220AC | | HFA08 | 3TB120 | | | |

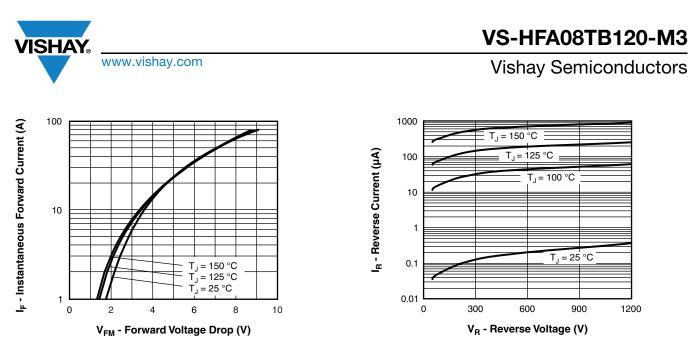
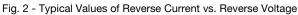


Fig. 1 - Maximum Forward Voltage Drop Characteristics



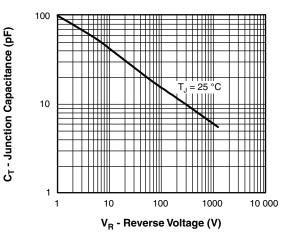


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

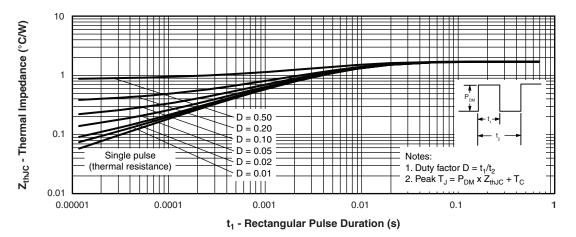
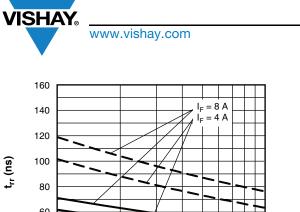


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



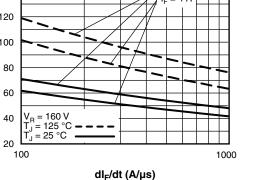


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

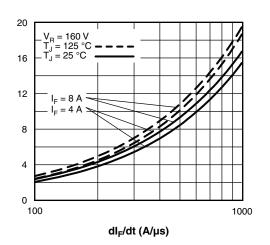
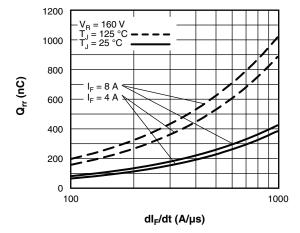


Fig. 6 - Typical Recovery Current vs. dl_F/dt





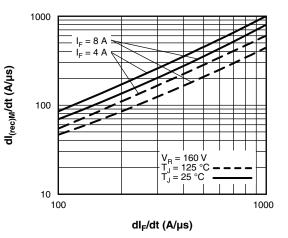


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

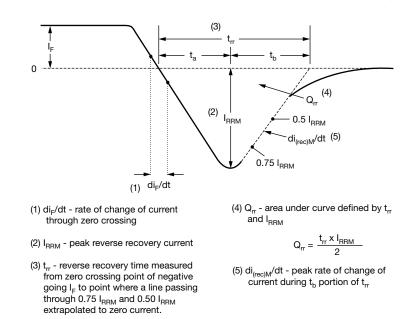


Fig. 9 - Reverse Recovery Waveform and Definitions

| Revision: 16-Dec-2021 | 4 | Document Number: 96189 |
|--|---|------------------------------------|
| For technical questions within your region | n: <u>DiodesAmericas@vishay.com</u> , <u>DiodesAsia@vishay.cc</u> | om, <u>DiodesEurope@vishay.com</u> |
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I_{rr} (A)

VS-HFA08TB120-M3

Vishay Semiconductors

VS-HFA08TB120-M3



ORDERING INFORMATION TABLE

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SHAY

| Device code | VS- | HF | Α | 08 | тв | 120 | -МЗ |
|-------------|------------|-------|-------------------------------|------------------------|----------|--------|---------|
| | | 2 | 3 | 4 | 5 | 6 | 7 |
| | 1 · 2 · | | nay Sem KFRED [®] | niconduo family | ctors pr | oduct | |
| | 3 - | Elec | ctron irra | , | 9 (1) | | |
| | 5 | - Pac | kage: | | , | | |
| | 6 | . – | | -220AC ng (120 | | V) | |
| | 7 - | | | ntal digit gen-free | | compli | ant and |

| ORDERING INFORMATION (Example) | | | | | |
|--------------------------------|---------------|-------------------------|--|--|--|
| PREFERRED P/N | BASE QUANTITY | PACKAGING DESCRIPTION | | | |
| VS-HFA08TB120-M3 | 50 | Antistatic plastic tube | | | |

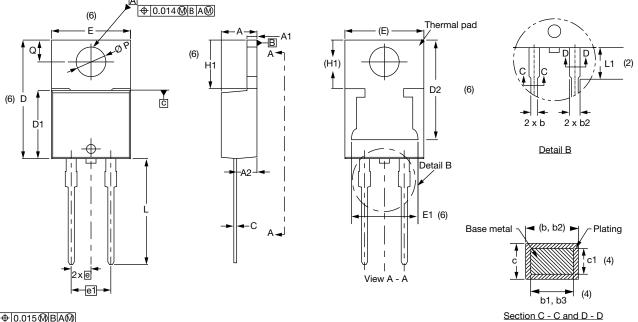
| LINKS TO RELATED DOCUMENTS | | | | |
|----------------------------|--------------------------|--|--|--|
| Dimensions | www.vishay.com/doc?96156 | | | |
| Part marking information | www.vishay.com/doc?95391 | | | |



Vishay Semiconductors

TO-220AC 2L

DIMENSIONS in millimeters and inches



⊕0.015@BA@



| SYMBOL | MILLIN | IETERS | INC | HES | NOTES |
|--------|--------|--------|-------|-------|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| A | 4.25 | 4.65 | 0.167 | 0.183 | |
| A1 | 1.14 | 1.40 | 0.045 | 0.055 | |
| A2 | 2.50 | 2.92 | 0.098 | 0.115 | |
| b | 0.69 | 1.01 | 0.027 | 0.040 | |
| b1 | 0.38 | 0.97 | 0.015 | 0.038 | 4 |
| b2 | 1.20 | 1.73 | 0.047 | 0.068 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 |
| С | 0.36 | 0.61 | 0.014 | 0.024 | |
| c1 | 0.36 | 0.56 | 0.014 | 0.022 | 4 |
| D | 14.85 | 15.35 | 0.585 | 0.604 | 3 |
| D1 | 8.38 | 9.02 | 0.330 | 0.355 | |

| Conforms to JEDEC | ® outline TO-220AC |
|-------------------|--------------------|
| | |

| SYMBOL | MILLIN | IETERS | INC | HES | NOTES |
|--------|--------|--------|-------|-------|-------|
| STMBOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| D2 | 11.68 | 13.30 | 0.460 | 0.524 | 6, 7 |
| E | 10.11 | 10.51 | 0.398 | 0.414 | 3, 6 |
| E1 | 6.86 | 8.89 | 0.270 | 0.350 | 6 |
| е | 2.41 | 2.67 | 0.095 | 0.105 | |
| e1 | 4.88 | 5.28 | 0.192 | 0.208 | |
| H1 | 6.09 | 6.48 | 0.240 | 0.255 | 6 |
| L | 13.52 | 14.02 | 0.532 | 0.552 | |
| L1 | 3.32 | 3.82 | 0.131 | 0.150 | 2 |
| ØР | 3.54 | 3.91 | 0.139 | 0.154 | |
| Q | 2.60 | 3.00 | 0.102 | 0.118 | |
| | | | | | |

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

Revision: 22-Feb-2024

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⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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